Theory of defect production in nonlinear quench across a quantum critical point

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We study defect production in a quantum system subjected to a nonlinear power law quench which takes it either through a quantum critical or multicritical point or along a quantum critical line. We elaborate on our earlier work \mathbb{D} . Sen, K. Sengupta, S. Mondal, Phys. Rev. Lett. 101, 016806 (2008)] and present a detailed analysis of the scaling of the defect density n with the quench rate and exponent for each of the above-mentioned cases. We also compute the correlation functions for defects generated in nonlinear quenches through a quantum critical point and discuss the dependence of the amplitudes of such correlation functions on the exponent . We discuss several experimental system s where these theoretical predictions can be tested.

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I. IN TRODUCTION

Quantum phase transitions have been widely studied in di erent system s for several years¹. Such transitions occur when the ground state of a quantum system changes due to the variation of some system parameter such as pressure², doping³ or magnetic eld^4 . More recently, non-equilibrium physics around such critical points has also been studied^{5,6}. In particular, quench dynamics through quantum critical points has been a subject of intense theoretical study in recent years. Such a dynam ics involves the tim e evolution of a param eter (t) in the Hamiltonian of the system which carries it through a quantum critical point, characterized by the correlation length exponent and the dynam ical critical exponent z, at = c. Since the energy gaps between the ground and the rst excited states vanish at the quantum critical point, the dynamics of the system necessarily becom es non-adiabatic in a nite region around this point even for an arbitrarily slow quench. This leads to the failure of the system to follow the instantaneous ground state. A s a result defects are produced^{7,8,9}. M ost of the initial studies of defect production in quench dynam ics for various quantum system s have been restricted 1 to the case of a linear quench (t) ot= , where is the quench rate 6,10,11,12,13,14,15,16,17,18,19,20,21,22 . It is well known that for a slow linear quench, the defect dend = (z + 1) where d is the dimension of the sitv n system 23,24. M ore recently, nonlinear power law quenches characterized by $(t) = _{0} t = j sign(t)$, where denotes the power law exponent and sign is the signum function, have also been studied $2^{5,26}$. In particular, it has been shown in Ref. 25, that if, during the quench, the critical point is reached at time t = 0 [$t = t_0 \in 0$], then the defect density n for such a quench process scales as d=(z + 1), where g g⁽¹⁾⁼ = d = (z + 1) [n n is a non-universal constant.]

On the experimental side, trapped ultracold atoms in optical lattices have provided ways to realize many interacting quantum systems with a variety of low temperature phases separated by quantum critical points^{27,28}.

These systems provide an easy access to non-equilibrium dynam ics of its constituent atom s and hence provide ideal experimental test beds for quench related studies. D effect production has already been studied experimentally for a spin-1 Bose condensate²⁹. However, a detailed experimental study of nonlinear quench dynamics has not been undertaken so far.

In this paper we study defect production due to nonlinear power law quenches in quantum critical systems. Our main results are the following. First, we elaborate on the work of Ref. 25 and provide a detailed derivation of the scaling laws of the defect densities mentioned above. Second, we extend the scaling law for defect production through multicritical points, as studied for a linear quench in Ref. 21, to nonlinear quenches. Third, m otivated by the work in Ref. 20, we derive scaling laws for defect densities produced during a nonlinear quench when the system is taken along a gapless line during the quench. Our results extend those in Ref. 21 and 20, and reproduce them as special cases. Fourth, taking the onedim ensionalK itaev m odelas a speci c system, we com pute the correlation functions for defects produced during a nonlinear quench. W e also provide a generalm odel independent discussion of the behavior of such correlation functions. Finally, we present a detailed discussion of possible experim ental system s where these theoretical results m ay be tested.

The organization of the paper is as follows. In Sec. II we provide detailed derivations for the scaling laws of defect density produced during a nonlinear quench. This is followed, in Sec. III, by a computation of the defect correlation functions. Next, in Sec. IV, we provide numerical studies to corroborate our analytical results. In Sec. V, we discuss possible experimental systems where the scaling laws derived in Sec. II can be tested. Finally we conclude in Sec. VI.

II. DEFECT PRODUCTION RATE IN A NONLINEAR QUENCH

The density of defects produced in a quench process depends crucially on the nature of the phases that the system passes through during the quench. Such processes can therefore be broadly classi ed into three types. First, the system may pass from one gapped phase to another through an interm ediate gapless critical or multicritical point. Second, the system may move along a gapless critical line in the parameter space so that at each point on that line the gap vanishes at a xed and unique m om entum ^{19,20}. Third, the quench m ay take the system from a gapped phase to another through a gapless hypersurface in parameter space as well as in m om entum space¹⁸. In what follows, we will study defect production during nonlinear quench of the st two types in Secs. IIA, IIB and IIC. An analogous study for the third case, where the system passes through a hypersurface in momentum space, is beyond the scope of the present work.

A. Quench dynam ics from one gapped phase to another

We start with the model Hamiltonian for a ddimensional system

$$H_{k}(t) = \begin{cases} X \\ K \\ R \end{cases} H_{k}(t) = \begin{pmatrix} Y \\ R \end{pmatrix} H_{k}(t) \\ K \end{pmatrix}_{3} + (K)_{4} + (K) ; (1)$$

where b(k) and (k) are model-dependent functions, i denote usualPaulim atrices, $(t) = _0 j= j$ sign(t) is the quench parameter where = 1 in plies linear quench, and $_k = (c_{1k}; c_{2k})$ represents the ferm ionic operators. Such a H am iltonian is known to represent several one- and two-dim ensional spin m odels such as the Ising¹, the X Y¹⁴ and the extended K itaev m odel^{18,31,32}. The instantaneous energies of the H am iltonian given by Eq. (1) are given by

$$E(\tilde{K}) = ((t) + b(\tilde{K}))^{2} + j(\tilde{K})f: (2)$$

These energy levels touch each other att = t_0 and $\tilde{k} = \tilde{k}_0$, so that j(\tilde{k}) j \tilde{k} \tilde{k}_0 j and $j_0 j = p \tilde{k}_0 = 0 j^{\dagger} = g^{\dagger}$, where $g = p (\tilde{k}_0) = 0$ j is a non-universal modeldependent parameter. At this point the energy levels cross and we have a quantum critical point with z = 1. Note that the critical point is reached at t = 0 only if $b(\tilde{k}_0)$ vanishes.

Let us rst consider the case where $b(\tilde{k}_0) = 0$ so that the system passes through the critical point at t = 0. In what follows, we shall assume that $j(\tilde{k})j$ \tilde{k} , $\tilde{k}_0 j$ and $b(\tilde{k})$ \tilde{k} , $\tilde{k}_0 \tilde{f}^1$ at the critical point, where z_1 1 so that E \tilde{K}_0 jand z = 1. In the rest of the analysis, we set ~ = 1, and scale t! t₀, ! ₀, (\tilde{K}) ! (\tilde{K}) = ₀, and b(\tilde{K}) ! b(\tilde{K}) = ₀.

We begin by observing that the ground state of the system must be $(c_{1k}; c_{2k}) = (1;0) [(0;1)]$ at the beginning [end] of the quench at t = 1 [1]. Thus the probability of defect form ation, is, the probability for the system to be in the excited state at the end of the quench for a given state jkim ust be given by

$$p_{k} = \lim_{t \le 1} j_{t}(t) j^{2}$$
 (3)

The density of these defects is thus given by

$$n = \lim_{t! \ 1} \sum_{BZ} \frac{d^{d}k}{(2)^{d}} \dot{F}_{1k}(t) \dot{f}; \qquad (4)$$

where $_{\rm B\,Z}$ denotes integration over the B rillouin zone.

To obtain p_{k} , we study the time evolution of the system which is governed by the Schrödinger equation i@ $_{k}=0t=H_{k}$; this leads to the following equations,

$$i\underline{c}_{1\bar{k}} = (j = j \operatorname{sign}(t) + b(\bar{k}))c_{1\bar{k}} + (\bar{k})c_{2\bar{k}};$$

$$i\underline{c}_{2\bar{k}} = (j = j \operatorname{sign}(t) + b(\bar{k}))c_{2\bar{k}} + (\bar{k})c_{1\bar{k}};$$
(5)

where we have kept the time dependence of $c_{1\tilde{k}\ (2\tilde{k})}$ (t) in plicit, and $\underline{c}_{1\tilde{k}\ (2\tilde{k})}$ (K) $(c_{1\tilde{k}\ (2\tilde{k})}$. To solve these equations, we de ne

$$C_{1k}^{0} = C_{1k} e^{j\int^{t} dt^{0}(jt^{0} = j \operatorname{sign}(t^{0}) + b(k))}$$

$$C_{2k}^{0} = C_{2k} e^{j\int^{t} dt^{0}(jt^{0} = j \operatorname{sign}(t^{0}) + b(k))} : (6)$$

Then substituting Eq. (6) in Eq. (5) and eliminating $c_{2\kappa}$ from the resulting equations, we get

$$c_{1k}^{\circ}$$
 2i [$t = jsign(t) + b(k)$] c_{1k}°
+ j (k) $f c_{1k}^{\circ} = 0$: (7)

Now we scale t! t =(+1) so that Eq. (7) becomes

$$c_{1k}^{\circ} = 2i [tj sign (t) + b(k)]^{= (+1)}] c_{1k}^{\circ} + j (k) j^{2} e^{-(+1)} c_{1k}^{\circ} = 0; \qquad (8)$$

From Eq. (8) we immediately note that since c_{1k} and $\dot{c_{1k}}$ di er only by a phase factor, p_{k} must be given by

$$p_{k} = \lim_{t \le 1} \frac{1}{p_{1k}^{0}} (t)^{2} = f [b(k)]^{\frac{1}{1}}; j(k)^{2} \frac{2}{1}]; (9)$$

where f is a function whose analytical form is not known for \notin 1. Nevertheless, we note that for a slow quench (large), p_k becomes appreciable only when the instantaneous energy gap, as obtained from Eq. (2), becomes small at some point of time during the quench. Consequently, f must vanish when either of its arguments are large: f(1;a) = f(a;1) = 0 for any value of a. Thus for a slow quench (large), the defect density n is given by

$$n = \int_{BZ}^{Z} \frac{d^{d}k}{(2)^{d}} f[b(\tilde{k})]^{\frac{1}{1}}; j(\tilde{k})^{\frac{2}{2}} \frac{2}{(1)}; \quad (10)$$

and receives its main contribution from values of f near κ = κ_0 where both b(k) and (k) vanish. Thus one obtains, after extending the range of momentum integration to 1 ,

$$n' \frac{Z}{(2)^{d}} f^{h} \tilde{F} \tilde{K}_{0} \tilde{f}^{1} \xrightarrow{+1}; \tilde{F} \tilde{K}_{0} f^{2} \xrightarrow{\frac{2}{+1}} i: (11)$$

Now scaling \tilde{K} ! (\tilde{K} \tilde{K}_0) $^{=(\ +\ 1)}$, we nd that

$$n = \frac{\frac{d}{d}}{\frac{d}{d}} \frac{Z}{(2)^{d}} f(\mathfrak{F}_{1}^{\mathfrak{F}_{1}})^{(1-z_{1})=(+1)};\mathfrak{F}_{1}^{\mathfrak{F}_{1}})$$

$$, \frac{\frac{d}{d}}{\frac{d}{d}} \frac{Z}{(2)^{d}} f(0;\mathfrak{F}_{1}^{\mathfrak{F}_{1}})^{(1-z_{1})=(+1)};\mathfrak{F}_{1}^{\mathfrak{F}_{1}})$$
(12)

where in arriving at the last line, we have used $z_1 > 1$ and ! 1. (If $z_l = 1$, the integral in the rst line is independent of , so the scaling argument still holds). Note that for = 1, Eq. (12) reduces to its counterpart for a linear quench^{23}. It turns out that the case $z_l < 1$ deserves a detailed discussion which we defer till Sec. IIB.

Next we generalize our results for a critical point with arbitrary values of and z. To this end, we consider a generic time-dependent H am iltonian H₁[t] H₁[(t)], whose states are labeled by β i and β i denotes the ground state. If there is a second order phase transition, the basis states change continuously with time during this evolution and can be written as

$$j (t)i = a_{\tilde{k}} (t) \tilde{j} [(t)]i:$$
(13)

The defect density can then be obtained in term s of these coe cients a $_{\rm F}$ (t) as

$$n = \frac{X}{p_{k \in 0}} (t! 1)^{2}; \qquad (14)$$

Following the analysis in Ref. 23, one can then obtain an expression for the defect density n as

n'
$$\frac{d^{d}k}{(2)^{d}} \int_{1}^{2} dh \tilde{\kappa} j \frac{d}{d} Die^{i \int d^{\circ} E_{\kappa} (0)^{2}};$$
 (15)

where $E_{\kappa}() = E_{\kappa}() = E_{\kappa}()$ are the instantaneous excitation energies, and we have replaced the sum over $\tilde{\kappa}$ by a d-dimensionalmomentum integral. We note, following Ref. 23, that near a critical point,

$$E_{\kappa}() = F(=j \tilde{\kappa} \quad \tilde{\kappa}_0 f); \quad (16)$$

where is the energy gap, z is the dynam ical critical exponent, and F (x) 1=x for large x. A lso, since the quench term vanishes at the critical point, $j j^{z}$ for a nonlinear quench, one can write

$$E_{\kappa}() = j j^{z} F^{0}(j j^{z} = j \tilde{\kappa} \tilde{\kappa}_{0} \tilde{f}); \qquad (17)$$

where $F^{0}(x)$ 1=x for large x. Further, one has $h\tilde{k}\frac{jd}{d}$ $Di = \tilde{j}\tilde{k} \quad \tilde{k}_{0}j^{z}G (=j\tilde{k} \quad \tilde{k}_{0}j^{z})$ near a critical point, where G (0) is a constant. This allows us to write

$$\hbar \tilde{\kappa} \frac{j}{d} \tilde{\mathcal{D}} i = \frac{z^{-1}}{\tilde{r} \tilde{\kappa}_0 \tilde{r}} G^0 (z^{-1} = \tilde{r} \tilde{\kappa}_0 \tilde{r}); \quad (18)$$

where G⁰(0) is a constant^{1,23}. Substituting Eqs. (17) and (18) in Eq. (15) and changing the integration variables to = ${}^{=(z + 1)}$ f \tilde{K}_0 j and = f \tilde{K}_0 j ${}^{1=()}$, we nd that

n ' C
$$d=(z+1)$$
; (19)

where ${\tt C}$ is a non-universal number independent of % $% {\tt C}$.

Next we focus on the case where the quench term does not vanish at the quantum critical point for $\tilde{k} = \tilde{k}_0$. We again consider the H am illionian H $_{\tilde{k}}$ (t) in Eq. (1), but now assume that the critical point is reached at $t = t_0 \notin 0$. This renders our previous scaling argument invalid since $(\tilde{k}_0) = 0$ but $b(\tilde{k}_0) \notin 0$. In this situation, $t_0 = j = g^{l=1}$ so that the energy gap E m ay vanish at the critical point for $\tilde{k} = \tilde{k}_0$. We now note that the most important contribution to the defect production comes from times near t_0 and from momenta near k_0 . Hence we expand the diagonal terms in H $_{\tilde{k}}$ (t) about $t = t_0$ and $\tilde{k} = \tilde{k}_0$ to obtain

$$H^{0}(t) = \begin{array}{c} X & h \\ & y(k) & g^{(1)=} & \frac{t t}{k} + b^{0}(k) \\ & & \\ & & \\ & & \\ & & + (k)_{+} + (k) & (k); \quad (20) \end{array}$$

where $b^0(\tilde{K})$ represents all the term s in the expansion of $b(\tilde{K})$ about $\tilde{K} = \tilde{K}_0$, and we have neglected all term s

$$R_{n} = (n+1)(n+2):::()$$

$$g^{(n)=} j(t + b) = \frac{n}{2} \operatorname{sign}(t) = n! \quad (21)$$

for n > 1 in the expansion of (t) about t_0 . We shall justify neglecting these higher order terms shortly.

Eq. (20) describes a linear quench of the system with $_{\rm e}$ () = =(g⁽¹⁾⁼). Hence one can use the well-known results of Landau-Zener dynam ics³⁰ to write an expression for the defect density,

$$n = \int_{BZ}^{Z} \frac{d^{d}k}{(2)^{d}} p_{k} = \int_{BZ}^{Z} \frac{d^{d}k}{(2)^{d}} \exp[-j(k)^{2} p_{e}(k)] (22)$$

For a slow quench, the contribution to n com es from $\tilde{\kappa}$ near $\tilde{\kappa}_0$; hence

n
$$e()^{d=2} = g^{(1)=} = (23)$$

Note that for the special case = 1, we get back the familiar result n $d^{=2}$, and the dependence of n on the non-universal constant g vanishes. A lso, since the quench is e ectively linear, we can use the results of R ef. 23 to nd the scaling of the defect density when the critical point at t = t₀ is characterized by arbitrary and z,

n
$$g^{(1)=} = \frac{d^{d}(z+1)}{d^{d}(z+1)}$$
: (24)

Next we justify neglecting the higher order term s R_n. We note that signi cant contributions to n come at times t when the instantaneous energy levels of H ⁰(t) in Eq. (20) for a given K are close to each other, i.e., (t t₀)= (K). A lso, for a slow quench, the contribution to the defect density is substantial only when p_{K} is signi cant, namely, when j (K)² 1 = e (). Using these arguments, we see that

$$R_{n} = R_{n-1} = (n + 1)g^{1} (t + b) = (n)$$

(n + 1) = (n): (25)

Thus we not that all higher order terms $R_{n>1}$, which were neglected in arriving at Eq. (23), are unimportant in the lim it of slow quench (large).

The scaling relations for the defect density n given by Eqs. (19) and (24) represent the central results of this section. For such power law quenches, unlike their linear counterpart, n depends crucially on whether or not the quench term vanishes at the critical point. For quenches which do not vanish at the critical point, n scales with the same exponent as that of a linear quench, but is characterized by a modied non-universale ective rate e (). If, how ever, the quench term vanishes at the criticalpoint, we nd that n scales with a novel -dependent exponent d = (z + 1). For = 1, e () = and d = (z + 1) = d = (z + 1); hence both Eqs. (19) and (24) reproduce the well-known defect production law for linear quenches as a special case²³. We note that the scaling of n will show a cross-over between the expressions given in Eqs. (19) and (24) near some value of = 0which can be found by equating these two expressions; \mathfrak{k}_0)j^z ¹⁼ .For > 1, the scaling law thisyields ₀ will thus be given by Eq. (19) (Eq. (24)) for () 0. W e also note here that the results of this section assum es that the system passes from one gapped phase to another through a critical point and do not apply to quenches which take a system along a critical line^{18,19}. We shall dealwith this case in Sec. IIC.

In this section, we will consider the e ect of a nonlinear quench in a system of the form given in Eq. (1), except that we now take

b(
$$\tilde{k}$$
) \tilde{f} $\tilde{k}_0 \tilde{f}^1$; and (\tilde{k}) \tilde{f} $\tilde{k}_0 \tilde{f}^2$; (26)

so that the system passes through the critical point at t = 0. This will be a generalization of the discussion in the rst part of Sec. IIA where we had $z_1 > z_2$ with $z_2 = 1$. We will see below that a separate analysis is required if $z_2 > z_1$. As discussed recently in Ref. 21, such a condition arises at the multicritical point of a one-dimensional spin-1/2 X Y model in a transverse eld; in that model, we nd that $z_1 = 2$ and $z_2 = 3$.

We begin our analysis by comparing the diagonal and o -diagonal terms in Eq. (1). From general considerations, it is clear that defects are mainly produced when both j=j sign (t) + b(k) and j (k) jare of order 1 or less since this is when the instantaneous energy levels given by Eq. 2 are close to each other. We now consider the form s of b(k) and (k) given in Eq. (26). Two possibilities arise in the limit ! 1 and $f = k_0 j! 0$. (i) If $z_1 > z_2$, then j (k) jbeing of order 1 or less in plies that b(k) j (k) j namely, b(k) 1. In this case, we can ignore the term b(k) in Eq. (1). This is equivalent to saying that the rst argument of the scaling function f in Eq. (9) can be set equal to zero. Follow ing arguments

sim ilar to those leading up to Eq. (12), we then see that

n
$$d = [z_2 (+1)]$$
 (27)

which is independent of the value of z_1 .

the defect density scales as

(ii) If $z_2 > z_1$, then j (\tilde{k}) j being of order 1 or less in plies that b(\tilde{k}) j (\tilde{k}) j namely, b(\tilde{k}) 1. Thus b(\tilde{k}) always remains nite as we approach the critical point and cannot in general be neglected. In order to have j= j sign(t) + b(\tilde{k}) of order 1 or less, we must therefore have t 1. Let us de ne a time t₀ as j₀ = j = sign(t₀)b(\tilde{k}) = sign(t₀) j k \tilde{k}_0 j¹, where is an arbitrary non-universal constant. Thus

$$t_0 j = j j^{1=}$$
 f_{K} $\tilde{k}_0 j^{e_1=}$: (28)

In a spirit similar to Eq. (20), we now linearize the function j=j sign (t) + b(\tilde{k}) near t = t₀, as (j=j sign (t) $j_0=j$ sign (t₀)) = (t t₀) $j_0=j^{-1}=$ which, using Eq. (28), is equal to (t t₀) = $_{e}$ ($\tilde{\chi}$;) where

$$_{e}$$
 ($\mathbf{\tilde{x}j}$) $_{e}$ = $\mathbf{j}\mathbf{\tilde{j}}^{(1)=}$ $\mathbf{\tilde{x}}$ $\mathbf{\tilde{k}}_{0}\mathbf{j}^{z_{1}(1)=}$ = :
(29)

The e ective linearized H am iltonian can be written as

$$H_e = _3(t_b) = _e + \frac{1}{K} \tilde{K}_0 \int_{-1}^{2} (30)$$

and describes a linear quench with replaced by $_{\rm e}$ ($3\dot{\chi}$;). The corresponding defect density is therefore given by the Landau-Zener expression in Eq. (22). We nd that

$$p_{k} \exp [\tilde{k}_{j} \tilde{k}_{0} j^{2z_{2} z_{1}(1 1=)} j j^{-1} =];$$
(31)

and

n
$$d = [2z_2 + z_1(1)]$$
: (32)

Note that the defect density obtained in Eq. (32) scales with an exponent which is independent of the non-universal coe cient .

To generalize these results for models with arbitrary $z_1 < z_2$ and , we notice that such models can be described by an elective H am iltonian H $_{\rm e}$ ((t)), where (t) = (t $\tau_{\rm b})$ = $_{\rm e}$ ($\tilde{\chi}$;) and $_{\rm e}$ ($\tilde{\chi}$;) is given by Eq. (29). This elective H am iltonian therefore describes a linear quench with a dilement $_{\rm e}$ for each $\tilde{\kappa}$ mode and with elective dynamical critical exponent z_2 and correlation length exponent %. Thus using the arguments of R ef. 23, we get

n'
$$\frac{d^d k}{(2)^d} \int_{1}^{2^1} dh \tilde{k} j \frac{d}{d} \tilde{p} i e^{i eff(\tilde{k}; j_r)} \int d^0 E_{\kappa} (0)^2;$$

(33)

where $E_{R}()$ ' $j \ J^{2} F^{0}(j \ J^{2} = J \tilde{K} J^{2})$, and $F^{0}(x)$ 1=x for large x. Further, one has $h \tilde{K} j_{d}^{d} J \tilde{D} i = J \tilde{K} j^{z_{2}} G(=j \tilde{K} J^{2})$ near a critical point, where G (0) is a constant. Using these relations, one obtains n ' $d^{d}k \ d^{0} {}^{0}z_{2} \ {}^{1}G({}^{0}) \exp \frac{i}{-} J \tilde{K} J^{(z_{2} + 1) + z_{1}} (1) = I \tilde{K}^{d} \tilde{J}^{(z_{2} + 1) + z_{1}} (1) = I \tilde{K}^{d} \tilde{J}^{(z_{2} + 1) + z_{1}} (1) = I \tilde{K}^{d} \tilde{J}^{(z_{2} + 1) + z_{1}} (1) = I \tilde{K}^{d} \tilde{J}^{(z_{2} + 1) + z_{1}} (1) = I \tilde{K}^{d} \tilde{J}^{(z_{2} + 1) + z_{1}} (1) = I \tilde{K}^{d} \tilde{J}^{(z_{2} + 1) + z_{1}} (1) = I \tilde{K}^{d} \tilde{J}^{(z_{2} + 1) + z_{1}} (1) = I \tilde{K}^{d} \tilde{J}^{(z_{2} + 1) + z_{1}} (1) = I \tilde{K}^{d} J^{(z_{2} + 1) + z_{1}} (1) = I \tilde{K}^{d} J^{(z_{2} + 1) + z_{1}} (1) = I \tilde{K}^{d} \tilde{J}^{(z_{2} + 1) + z_{1}} (1)$, where $I = I \tilde{K} J^{(z_{2} + 1) + z_{1}} (1) = I \tilde{K}^{d} J^{(z_{2} + 1) + z_{1}} (1)$, one nally gets

$$d = [(z_2 + 1) + z_1 (1)];$$
(34)

which reduces to Eq. (32) for $z_2 = 1$. Note that for Eq. (27), a generalization to models with arbitrary z_2 is straightforward, and is given by Eq. (19) with z replaced by z_2 .

n

Eqs. (27), (32) and (34) are the main results of this section. These results generalize those in Sec. IIA to defect production for quenches through arbitrary multicritical points. Note that for $z_1 = z_2$, Eq. (27) and Eq. (32) agree for any value of , giving n $d = [z_2 (+1)]$. Further, for the case of linear quenching, = 1, these equations agree for any value of z_1 and z_2 , giving n

 $d^{d=(2z_2)}$ which has been recently obtained in Ref. 21.

C. Quench dynam ics along a gapless line

Recently quench dynam ics in a one-dimensional X Y model in the presence of a spatially modulated transverse magnetic eld has been studied in Ref. 20. Such a model is described by the H am iltonian

where J and are respectively the strength of and the anisotropy in the nearest neighbor spin-spin interactions, ^a (a = x;y;z) denote the Paulim atrices, and h and

denote the uniform and alternating components of the magnetic elds respectively. The phase diagram of this model is discussed in detail in R ef. 20. It was pointed out that quenching the anisotropy parameter $(t) = _0 t =$ linearly while sitting at the paramagnetic phase determined by the condition $h^2 = ^2 + J^2$, leads to a time evolution of the system along a gapless line. It was also show n, via mapping this spin model to a system of M a jorana fermions by a Jordan-W igner transform ation, that the evolution of the m odel described by Eq. (35) can be represented by an elective H am iltonian given by²⁰

$$H_{e}(k;t) = \bigvee_{k}^{Y} \sim (t)k_{3} + Jk^{2}_{1} \quad k; \quad (36)$$

where $_{k} = (c_{1k}; c_{2k})$ is the usual two component fermionic eld, $\sim (t) = (t)J^{2} + J^{2}$ and $J^{*} = J^{2} + J^{2}$. The quench dynamics of this model was studied in Ref. 20 for the linear quench $(t) = _{0}t^{2}$ using the Landau-Zener form alism. It was found that the defect density scales as

n

Note that since for this model z = = 1, the naive expectation according to the analysis of Sec. IIA is to have n 1^{\pm} . This result therefore clearly points out the necessity of extending the analysis of Sec. IIA for quenches along gapless lines in parameter space. In what follow s, we shall only restrict ourselves to quenches where the gap vanishes at the same momentum value k_0 ; $k_0 = 0$ for the present case.

W e start with a generic d-dimensionalm odel described by a H am iltonian

$$H_{e}(k;t) = \bigvee_{k}^{y} (t) \tilde{x} \tilde{f}_{3} + {}_{0} \tilde{x} \tilde{f}_{1} {}_{k};(38)$$

where (t) = $_{0}$ j= j sign (t) is the quench parameter, a and b are arbitrary exponents, and we have taken $\tilde{k}_{0} = 0$ for clarity. Note that d = a = 1 and b = 2 corresponds to the X Y m odel studied in Ref. 20, while a = 0 and d = b = 1 corresponds to the one-dimensional K itaev m odel studied in Ref. 18. For a \neq 0, the system passes along a gapless line during the quench. We study the time evolution of the model in a manner sim ilar to that described in Sec. IIA. After some straightforward algebra, one obtains the equation for the evolution of c_{1k}^{0} (t) = c_{1k} (t) exp (i t_{1}^{k} dt t_{2}^{0} = j sign (t) \tilde{K}_{1}^{n}) as

$$c_{1\bar{k}}^{\circ}$$
 2ij= jsign (t) $\tilde{k} f c_{1\bar{k}}^{\circ} + c_{0}^{\circ} \tilde{k} f^{\circ} c_{1\bar{k}}^{\circ} = 0$: (39)

Next we de ne $_{k} = =k^{a=}$ and scale t! $t_{k}^{=(+1)}$ in Eq. (39) to obtain

$$c_{1k}^{0} = 2i j sign(t) c_{1k}^{0} + j j_{0}^{2} \tilde{k} j^{2b} \frac{2a}{+1} \frac{2}{+1} c_{1k}^{0} = 0:$$
(40)

From Eq. (40), we not that the probability of defect form ation for a given momentum \tilde{K} must be given by

$$p_{k} = \lim_{t \ge 1} \dot{\mathcal{F}}_{1k}^{0}(t) \dot{f} = f \begin{bmatrix} 2 \\ 0 \\ \mathcal{F} \dot{f} \\ \mathcal{F} \end{bmatrix}^{2b} 2^{a=(+1)} 2^{a=(+1)}];$$
(41)

where f[1] = 0. The defect density therefore becomes

n
$$\frac{Z}{\frac{d^{d}k}{(2)^{d}}} f(\frac{2}{0}, \frac{2}{+1}, \tilde{k})^{2b} \frac{2a}{+1})$$
: (42)

U sing the same logic as outlined in Sec. IIA, we scale $\mathfrak{F}_{j!} = \overline{\mathfrak{F}_{j!}}^{\mathfrak{b}_{(+1)}} \mathfrak{F}_{j}$ and get

n
$$\frac{d}{b(+1)a}$$
: (43)

This result generates the scaling of the defect density derived in Ref. 20 (n $d^{(2b \ a)}$) for the special case = 1, and that of the one-dimensional K itaev model studied in Ref. 18 for = b = z = 1 and a = 0.

Finally, we generalize the result in Eq. (43) to system s where the energy di erence between the ground and excited states vanishes along the gapless line as $= {}^{c} \tilde{K} f$. Note that for the quenches treated in Sec. IIA, c = z. Here, how ever, since the quench takes place along a gapless line, c need not have the same interpretation and can be system speci c. Exactly at the quantum critical point $= {}_{c}$, the energy gap vanishes as $\tilde{K} f$. Thus b is to be interpreted as the dynam ical scaling exponent z in the present case. Then using the same e scaling argum ent as in Sec. IIA, we can express the defect density n using Eq. (15). How ever, in the present case the energy gap scales as

$$E_{k}() E_{0}() = F(=j_{k}j^{b});$$

 $h_{k}j_{d}^{d}j_{d}i = 1=j_{k}j_{G}(=j_{k}j^{b});$ (44)

where F (x) = 1=x for large x, and G (0) is a constant. U sing Eq. (44), we see that

$$E_{k}() \quad E_{0}() = {}^{c} \tilde{\chi}_{1}^{d} F({}^{c} \tilde{\chi}_{1}^{d} = \tilde{\chi}_{2}^{b});$$

$$h\tilde{\chi}_{1}^{d} Di = h\tilde{\chi}_{1}^{d} Di_{d}^{d} Di_{d}^{d};$$

$$' \frac{{}^{c} {}^{1}}{\tilde{\chi}_{1}^{b} {}^{a}} G \frac{{}^{c} \tilde{\chi}_{1}^{d}}{\tilde{\chi}_{2}^{b}} : (45)$$

Substituting these in Eq. (15), the defect density produced in this system is found to be

n
$$\stackrel{Z}{\underset{(2)^{d}}{\overset{d^{d}k}{\underset{1}{\overset{1}{5}j^{(b-a)}}{\overset{c}{5}j^{(b-a)}}G}}} \stackrel{!}{\underset{\tilde{F}^{b}}{\overset{c}{5}j^{(a-b)}}} e^{i\int_{a} d^{0} \cdot \hat{f}_{a} \cdot \hat{f$$

Dening new variables = $f_{ij}^{(a \ b)=c}$ and $f_{ij}^{\circ}^{\circ} = f_{ij}^{c=[(b \ a)+b \ c]}$, we get

n
$$d c = [(b a) + b c]$$
; (47)

Eq. (47) is one of the central results of this work, and it generates all the previous scaling laws for both linear and nonlinear quenches through critical lines and points (but not through multicritical points) as special cases. For a = 0, b = z and c = z, we recover the scaling law Eq. (19) for a nonlinear quench, whereas for = c = 1, we obtain the scaling law derived for a linear quench in Ref. 20.

III. DEFECT CORRELATION FUNCTIONS

For the purpose of computation of defect correlation functions, we are going to restrict ourselves to the class of d-dimensionalm odels given by H (t) in Eq. (1). A smentioned before, m any standard spin m odels in one and two dimensions can be m apped, via standard Jordan-W igner transform ations¹, to such ferm ionic m odels described by H (t). Let us denote the ground and the excited states of H (t) before the quench (at t = 1) by p_k and p_k respectively for a given value of K. Then the state of the system after the quench (at t = 1) is given by¹⁸

$$j i_{k} = p \frac{p_{k}}{p_{k}} j j i_{k} + p \frac{1}{1 p_{k}} j j i_{k}$$
 (48)

U sing this, one can compute the defect correlation functions for these models. These correlation functions are of two types. They can either vanish at the origin, as in the case of the two-dimensional extended K itaev model¹⁸, or can be written as^{10,18}

$$M_{r}i = r_{;0} + C \qquad d^{d}kf[j(R)_{j}^{2}]^{\frac{2}{r+1}}]g(R r); (49)$$

where $O_r = i_{R-R+r}$, a denotes the eld operators for M ajorana fermions, g(K r) is a system speci c function independent of ,C denotes a system and dimension speci c constant which will be unimportant for subsequent discussions, and we have used Eq. (9) to obtain the value of p_R . Since for a slow quench, p_R is appreciable only near $K = K_0$, we expand (K) about K_0 , scale the momentum components $k_i^0 = (k - k_0)_i^{-(r+1)}$, and extend the range of integration to 1 to get

$$hO_{\mathfrak{x}}\mathbf{i} = \underset{\mathfrak{x};0}{\mathbf{c}} + \frac{\mathbf{C}}{\mathbf{d} = (+1)} \int_{0}^{Z_{1}} d^{d}\mathbf{k}^{0} \mathbf{f} [\mathbf{\tilde{k}}^{\circ} \mathbf{\tilde{f}}] g(\mathbf{\tilde{k}}^{\circ} \mathbf{\tilde{k}}^{\circ}) \mathbf{\tilde{k}};$$
(50)

where $\mathbf{r}_i^{\circ} = \mathbf{r}_i = {}^{=(+1)}$. Thus we nd that quite generally, for the class of models whose defect correlation functions do not vanish at the origin,

$$\ln (1 + h_{x=0}) = \ln (C^{0}) - \frac{d}{1+1} \ln ();$$
 (51)

i.e., the logarithm of the deviation of the amplitude of these correlation functions at the origin from 1 is a linear function of ln() with a slope of d = (+1).



FIG.1: Plot of hO_r ivs r for = 2 (black dot-dashed line), = 3 (red dashed line), = 4 (blue solid line), and = 20.

W e now compute the correlation function for a speci c m odel, nam ely, the one-dim ensionalK itaev m odel [18,25, 33] which has the H am iltonian

$$H = \begin{matrix} X \\ J_1 S_i^{x} S_{i+1}^{x} + J_2 S_i^{y} S_{i-1}^{y} \end{matrix}; (52)$$

where J_1 and J_2 denote the nearest neighbor interaction strengths, and S_i denotes the spin at site i. U sing the standard Jordan-W igner transform ation, this H am iltonian can be mapped on to a free ferm ionic H am iltonian [18,25,33]

Here $J = J_1$ J_2 , and $k = (c_1 (k); c_2 (k))$ are the ferm ionic elds. The Ham iltonian is changed in time by varying the parameter J keeping J_+ xed. The defect correlation function for this model is given by [18]

$$\text{bo}_{ri} = \frac{2}{r;0} + \frac{2}{0} \frac{Z}{dk \, p_k \, \cos(kr)}$$
 (54)

Thus we not that the defect correlation functions have the same form as in Eq. (49) with C = 2= and $g = \cos(kr)$. A plot of the correlation function as a function of r, sans the -function peak at the origin, is shown in Fig. 1 for = 20 and several representative values of .

IV . NUMERICAL EVALUATION OF DEFECT $\label{eq:constraint} \mathsf{DENSIT}\ \mathsf{I\!ES}$

In this section, we provide num erical studies of the onedim ensional Ising and K itaev m odels to supplement our



FIG. 2: Variation of the defect density n with the quench exponent for representative values of = 10 (black solid line), = 15 (red dashed line) and = 20 (blue dotted line). A polynomial t of the form n = a ^b yields exponents which are very close to the theoretical result 1=2 for all values of (see text for details).

analytical results. First we consider the one-dimensional Ising model in a transverse eld described by

$$H_{Ising} = J \begin{pmatrix} X & X \\ S_{i}^{z} S_{i+1}^{z} + g & S_{i}^{x} \end{pmatrix}; (55)$$

where J is the strength of the nearest neighbor interaction, and g = h=J is the dimensionless transverse eld. In what follows, we shall quench the transverse eld as $g(t) = \frac{1}{2} = j$ sign (t) and compute the density of the resultant defects.

We begin by mapping H $_{\rm Ising}$ to a system of free ferm ions via a standard Jordan-W igner transform ation ^1

$$H^{\circ} = \int_{k}^{X} \int_{k}^{y} (g \cos(k))_{3} + \sin(k)_{1} k: (56)$$

If the external magnetic eld g is varied with time as $g(t) = g_0 = j sign(t)$, then the system will go through two quantum critical points at g = 1 and 1. The energy gap vanishes at these quantum critical points at $k = k_0 = 0$ and . As a result, defects are produced in non-adiabatic regions near these points. For this model, the quantum critical point is at $t = t_0 \notin 0$ and z = 1. Hence, e = 1 for both the quantum critical points. From Eq. (24), therefore, we expect the defect density produced in this system to be given by n $(=)^{1-2}$.

To verify this expectation, we numerically solve the Schrödinger equation $i \mathfrak{Q}_{t-k} = H_k(t)_k$ and obtain the probability p_k for the system to be in the excited state. Finally, integrating over all k within the Brillouin zone, we obtain the defect density n for di erent values of > 1 with xed . The plot of n as a function of for = 10; 15 and 20 is shown in Fig. 2. A to these



FIG.3: Plot of $\ln(n)$ vs $\ln()$ for the one-dimensional K itaev m odel for = 2 (black solid line), = 4 (red dotted line), = 6 (blue dashed line) and = 8 (green dash-dotted line). The slopes of these lines agree reasonably with the predicted theoretical values = (+ 1) as shown in the table.

curves gives the values of the exponents to be 0:506 0:006, 0:504 0:004 and 0:505 0:002 for = 10; 15 and 20 respectively which are remarkably close to the theoretical value 1=2. The system atic positive deviation of the exponents from the theoretical value 1=2 comes from the contribution of the higher order terms neglected in the derivation of Eqs. (23) and (24). We note that the region of validity of our linear expansion, as can be seen from Fig. 2, grows with which is in accordance with the result in Eq. (25).

Next, we consider the one-dimensional K itaev model which is governed by the Ham iltonian in Eq. (52). As mentioned in Sec. 54, such a model can also be mapped on to the free ferm ionic H am iltonian given by Eq. (53). This system passes through the quantum critical point at J = 0 for k = -2 when $J(t) = J_{t} = j_{sign}(t)$ is varied nonlinearly with time. Here the quantum critical point is at t = 0. Thus from Eq. (19) we expect the =(+1) since = z = 1 for this defect density n system. To check this prediction, we num erically solve the Schrödinger equation $i\theta_t$ (kg) = H⁰(k;t) (k;t) and compute the defect density n = $_0$ dk= p_k as a function of the quench rate for dierent with $x \in J_+ = J = 1$. A plot of ln (n) vs ln () for dierent values of is shown in Fig. 3. The slope of these lines, as can be seen from Fig. 3, changes from 0:67 towards 1 as increases from 2 towards larger values. This behavior is consistent with the prediction of Eq. (19). The slopes of these lines also show excellent agreem ent with Eq. (19) as shown in the inset of Fig. 3.

F inally, we illustrate the expressions in Eqs. (27) and (32) by taking two one-dimensional models governed by Eqs. (1) and (26) with $z_1 = 2$, $z_2 = 1$ and $z_1 = 1$, $z_2 = 2$ respectively. Setting = 4, we num erically carry out the time evolutions for dimensional models of the momentum



FIG. 4: Plots of $\ln(n)$ vs $\ln()$ for models with $z_1 = 2$ and $z_2 = 1$ (red dotted lower line) and $z_1 = 1$ and $z_2 = 2$ (black solid upper line), for d = 1 and = 4. The slopes of the lower and upper lines are 0.828 and 0.301 which compare reasonably with the predicted theoretical values of 4=5 = 0.8 and 4=13 = 0.308 respectively.

k and then integrate to compute the defect density as a function of . The results are shown in Fig.4; reasonable agreement is obtained with the theoretical values of the exponents given in Eqs. (27) and (32).

V. EXPERIMENTS

The generality of our results allows for their veri cation in several realizable experim ental system s. W e note that all our results have been obtained at zero tem perature with the assumption that the system does not relax signi cantly during the quench process and till the m easurem ent of the defect density has been perform ed. This might seem too restrictive. However, we would like to point out that systems of ultracold atoms in optical or magnetic traps and/or optical lattices can easily satisfy the required criteria since they have a very long relaxation time which often gets close to the system lifetim e^{27} . We list som e possible experiments brie y here. First, there has been a concrete proposal for the realization of the K itaev m odel using an optical lattice²⁸. In such a realization, all the couplings can be independently tuned using separate m icrowave radiations. In the proposed experiment, one needs to keep $J_3 = 0$ and vary $J_{1(2)} = J(1)$ j= jsign(t)=2, so that J_+ remains constant while J varies in time. The variation of the defect density, which in the experimental set-up would correspond to the bosons being in the wrong spin state, would then show the theoretically predicted power law behavior in Eq. (19). Secondly, a similar quench experiment can be carried out with spin-1 bosons in a magnetic eld described by an e ective Hamiltonian

 $H_{e} = c_{2}n_{0}hSi^{2} + c_{1}B^{2}hS_{z}^{2}i^{29}$, where $c_{2} < 0$ and n_{0} is the boson density. Such a system undergoes a quantum phase transition from a ferrom agnetic state to a polar condensate at B = $jc_2 jn_0 = c_1 \cdot A$ quench of the magnetic eld $B^2 = B_0^2 = j$ would thus lead to a scaling of the defect density with an elective rate $_{e}$ () = =(g⁽¹⁾⁼), where $q = \dot{q}_2 \dot{q}_0 = c_1$. A measurement of the dependence of the defect density n on should therefore serve as a test of the prediction in Eq. (24). Finally, spin gap dim er com pounds such as $BaCuSi_2O_6$ are known to undergo a singlet-triplet quantum phase transition at B_c ' 23:5T which is known to be very well described by the meaneld exponents z = 2 and $z = 2 = 3^{34}$. Thus a nonlinear quench of the magnetic eld through its critical value $B = B_c + B_0 = j sign(t) should lead to a scaling of the$ 6 = (4 + 3) in d = 3. In the experiment, defects n the defect density would correspond to residual singlets in the nal state which can be computed by measuring the total magnetization of the system immediately after the quench. W e note that for these dim er system s, it will be necessary to take special care to achieve the criterion of long relaxation tim e m entioned earlier.

- ¹ S.Sachdev, Quantum Phase Transitions (Cambridge University Press, Cambridge, 1999).
- ² P.Gegenwart, Q.Si, and F.Steglich, Nature Phys. 4, 186 (2008).
- 3 S.Sachdev, Nature Phys. 4, 173 (2008).
- ⁴ T.Giam archi, C.Ruegg, and O.Tchernyshyov, Nature Phys. 4, 198 (2008).
- ⁵ K.D am le and S.Sachdev, Phys. Rev. B 56, 8714 (1997); ibid Phys. Rev. Lett. 78, 943 (1997); S.A.Hartnoll, P. K.Kovtun, M.Mueller, and S.Sachdev, Phys. Rev. B 76, 144502 (2007); A.delMaestro, B.Rosenow, N.Shah, and S.Sachdev, Phys. Rev. B 77, 180501 (2008).
- ⁶ K.Sengupta, S.Powell, and S.Sachdev, Phys.Rev.A 69, 053616 (2004).
- ⁷ T.W.B.Kibble, Phys.A 9, 1387 (1976).
- ⁸ W .H.Zurek, Nature (London) 317, 505 (1985).
- ⁹ B.Damski, Phys. Rev. Lett. 95, 035701 (2005).
- ¹⁰ J. D ziam aga, Phys. Rev. Lett. 95, 245701 (2005); ibid Phys. Rev. B 74, 064416 (2006).
- ¹¹ P. Calabrese and J. Cardy, J. Stat. Mech: Theory Expt P04010 (2005), and Phys. Rev. Lett. 96, 136801 (2006).
- ¹² A .D as, K .Sengupta, D .Sen, and B .K .C hakrabarti, P hys. Rev. B 74, 144423 (2005).
- ¹³ R.W. Chemg and L. Levitov, Phys. Rev. A 73, 043614 (2006).
- ¹⁴ V.M ukherjee, U.D ivakaran, A.D utta, and D.Sen, Phys. Rev.B 76, 174303 (2007).
- ¹⁵ B.Dam ski and W.H.Zurek, Phys. Rev. A 73, 063405 (2006).
- ¹⁶ T.Caneva, R.Fazio, and G.E.Santoro, Phys. Rev. B 76, 144427 (2007).
- ¹⁷ F.M. Cucchietti, B.Damski, J.Dzianmaga, and W.H. Zurek, Phys. Rev. A 75, 023603 (2007).
- ¹⁸ K.Sengupta, D.Sen, and S.M ondal, Phys. Rev. Lett. 100, 077204 (2008); S.M ondal, D.Sen, and K.Sengupta, Phys.

VI. CONCLUSIONS

In conclusion, we have studied defect production in quantum critical systems for an arbitrary nonlinear power law quench. We have shown that the defect production rate depends crucially on whether the system passes from one gapped phase to another or along a critical gapless line during the quench. We have obtained general scaling laws for defect densities produced during the quench for both these cases, and have veri ed these laws by numerical studies of one-dimensional systems. We have also computed the defect correlation functions for a class of d-dimensional models and have discussed the scaling of the amplitude of these functions with the quenching rate. Finally, we have discussed several experimental systems where these results can, in principle, be tested.

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Rev.B 78,045101 (2008).

- ¹⁹ F.Pellegrini, S.M ontangero, G.E. Santoro, and R.Fazio, arX iv 0801.4475 (unpublished).
- ²⁰ U.D ivakaran, A.D utta, and D.Sen, arX iv 0805.3328 (un-published).
- ²¹ U. Divakaran, V. Mukherjee, A. Dutta, and D. Sen, arX iv:0807.3606 (unpublished).
- ²² D.Patane, A.Silva, L.Amico, R.Fazio, and G.E.Santoro arXiv:0805.0586 (unpublished).
- ²³ A.Polkovnikov, Phys.Rev.B 72, 161201(R) (2005).
- ²⁴ A. Polkovnikov and V. Gritsev, arX iv 0706.0212 (unpublished).
- ²⁵ D.Sen, K.Sengupta, and S.M ondal, Phys. Rev. Lett. 101, 016806 (2008).
- ²⁶ R.Barankov and A.Polkovnikov, arX iv:0804.2894 (unpublished).
- ²⁷ For a review, see I. Bloch, J. D alibard, and W. Zwerger, arX iv:0704.3011, to appear in Rev. M od. Phys.
- ²⁸ L.-M. Duan, E. Dem Ler, and M. D. Lukin, Phys. Rev. Lett. 91, 090402 (2003); A. M icheli, G. K. Brennen, and P. Zoller, Nature Physics 2, 341 (2006).
- ²⁹ L. E. Sadler, J. M. Higbie, S. R. Leslie, M. Vengalattore, and D. M. Stam per-Kum, Nature (London) 443, 312 (2006).
- ³⁰ See for exam ple, L. Landau and E. M. Lifshitz, Quantum M echanics: Non-relativistic Theory, 2nd Ed. (Pergam on P ress, O xford, 1965); S. Suzukiand M. O kada in Quantum Annealing and Related Optim ization M ethods, Eds. by A. D as and B.K. Chakrabarti (Springer-Verlag, Berlin, 2005).
- ³¹ H.-D. Chen and Z. Nussinov, J. Phys. A 41, 075001 (2008).
- ³² D.H.Lee, G.M. Zhang, and T.Xiang, Phys. Rev. Lett. 99, 196805 (2007).
- ³³ A.K itaev, Ann.Phys. 321, 2 (2006).
- ³⁴ S.E. Sebastian, P.A. Sharma, M. Jaime, N. Harrison, V. Correa, L. Balicas, N. Kawashima, C.D. Batista, and I.

R.Fisher, Phys.Rev.B 72, 100404(R) (2005).